

TRW

## AMENDMENT TRANSMITTAL LETTER

Docket No.  
FIS920030199US1

Application No. 10/604,607	Filing Date August 4, 2003	Examiner Thanh T. Nguyen	Art Unit 2813
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Applicant(s): Huajie Chen et al.

**STRUCTURE AND METHOD OF MAKING STRAINED SEMICONDUCTOR CMOS**  
**Invention: TRANSISTORS HAVING LATTICE-MISMATCHED SEMICONDUCTOR REGIONS**  
**UNDERLYING SOURCE AND DRAIN REGIONS (As Amended)**

### TO THE COMMISSIONER FOR PATENTS

Transmitted herewith is an amendment in the above-identified application.

The fee has been calculated and is transmitted as shown below.

#### CLAIMS AS AMENDED

	Claims Remaining After Amendment	Highest Number Previously Paid	Number Extra Claims Present	Rate	
Total Claims	31	32	0		
Independent Claims	3	- 3	0		
Multiple Dependent Claims (check if applicable) <input type="checkbox"/>					
Other fee (please specify):					
<b>TOTAL ADDITIONAL FEE FOR THIS AMENDMENT:</b>					

Large Entity

Small Entity

No additional fee is required for this amendment.

Please charge Deposit Account No. \_\_\_\_\_ in the amount of \$ \_\_\_\_\_.  
A duplicate copy of this sheet is enclosed.

A check in the amount of \$ \_\_\_\_\_ to cover the filing fee is enclosed.

Payment by credit card. Form PTO-2038 is attached.

The Director is hereby authorized to charge and credit Deposit Account No. 09-0458 as described below. A duplicate copy of this sheet is enclosed.

Credit any overpayment.

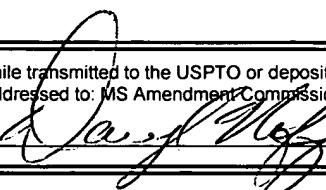
Charge any additional filing or application processing fees required under 37 CFR 1.16 and 1.17.

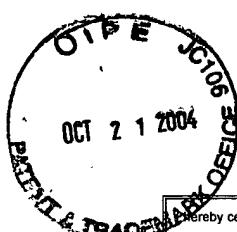
Dated: October 18, 2004

Daryl K. Neff  
Attorney Reg. No. 38,253

I hereby certify that this correspondence is being facsimile transmitted to the USPTO or deposited with the U.S. Postal Service with sufficient postage as First Class Mail, in an envelope addressed to: MS Amendment/Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on the date shown below.

Dated: October 18, 2004

Signature:  (Daryl K. Neff)



MS Amendment, Commissioner for Patents, Alexandria, VA 22313-1450 on this date: October 18, 2004

Name of Depositor:

Daryl K. Neff

Signature & Date

A handwritten signature in black ink, appearing to read "Daryl K. Neff" over the date "October 18, 2004".

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: <b>Huajie Chen, et al.</b>	Date: <b>October 18, 2004</b>
Serial Number: <b>10/604,607</b>	Examiner: <b>Thanh T. Nguyen</b>
Filed: <b>August 4, 2003</b>	Group Art Unit: <b>2813</b>
Title: <b>STRUCTURE AND METHOD OF MAKING STRAINED SEMICONDUCTOR CMOS TRANSISTORS HAVING LATTICE- MISMATCHED SEMICONDUCTOR REGIONS UNDERLYING SOURCE AND DRAIN REGIONS (As Amended)</b>	H. Daniel Schnurmann IBM Corporation D/18G, B/300, Zip 482 2070 Route 52 Hopewell Junction, NY 12533-6531

### AMENDMENT

MS Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

In response to the Office Action dated July 16, 2004, Applicants submit the following amendments and remarks for the Examiner's consideration.

Title of Invention:

Please amend the title to read:

STRUCTURE AND METHOD OF MAKING STRAINED SEMICONDUCTOR CMOS  
TRANSISTORS HAVING LATTICE-MISMATCHED SEMICONDUCTOR REGIONS  
UNDERLYING SOURCE AND DRAIN REGIONS